

30V N-Channel Enhancement Mode MOSFET

Voltage

30 V

Current

70 A

Features

- R_{DS(ON)}, V_{GS}@10V, I_D@10A<3.8mΩ
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_{D}@5A<5.5m\Omega$
- High switching speed
- Improved dv/dt capability
- Low gate charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.03 grams

DFN3333-8L

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	30	\/	
Gate-Source Voltage		V _{GS}	<u>+</u> 20	V	
Continuous Drain Current(Note 4)	Tc=25°C	I _D	70	A	
	Tc=100°C		44		
Pulsed Drain Current(Note 1)	T _C =25°C	I_{DM}	280		
Power Dissipation	Tc=25°C	Po	39	14/	
	Tc=100°C		15.6	W	
Continuous Danie Commont/Note (1)	T _A =25°C	l _D	16	А	
Continuous Drain Current(Note 4)	T _A =70°C		13		
Power Dissipation	T _A =25°C	6	2	10/	
Power Dissipation	T _A =70°C	PD	1.3	W	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Transical Theorems I Decistors as (Note 4.5)	Junction to Case	Rejc	3.21	°C/W	
Typical Thermal Resistance ^(Note 4,5)	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} , I _D =250uA	1	1.6	2.5	
Drain Source On State Registence	D	V _{GS} =10V, I _D =10A	-	3.3	3.8	mΩ
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =5A	-	5	5.5	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	Igss	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic ^(Note 6)			_			
Total Gate Charge	Qg	V _{DS} =15V, I _D =24A, V _{GS} =4.5V ^(Note 2,3)	-	23	-	nC
Gate-Source Charge	Qgs		-	8	-	
Gate-Drain Charge	Q_{gd}		-	9	-	
Input Capacitance	Ciss	V _{DS} =25V, V _{GS} =0V,	-	2436	-	pF
Output Capacitance	Coss		-	306	-	
Reverse Transfer Capacitance	Crss	f=1MHZ	-	196	-	
Turn-On Delay Time	td _(on)	V_{DS} =15V, I_{D} =15A, V_{GS} =10V, R_{G} =1 Ω	-	32	-	ns
Turn-On Rise Time	t _r		-	169	-	
Turn-Off Delay Time	td _(off)		-	232	-	
Turn-Off Fall Time	t _f	(100 2,0)	-	170	-	
Drain-Source Diode						
Maximum Continuous Drain-Source				-	70	A
Diode Forward Current	I _S		_			
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V	-	0.66	1	V

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

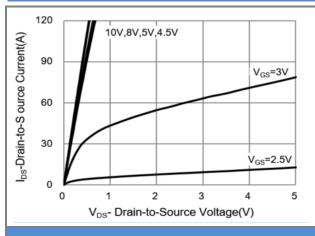


Fig.1 On-Region Characteristics

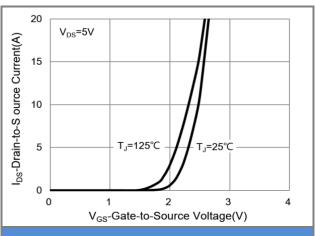


Fig.2 Transfer Characteristics

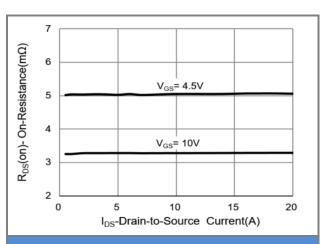


Fig.3 On-Resistance vs. Drain Current

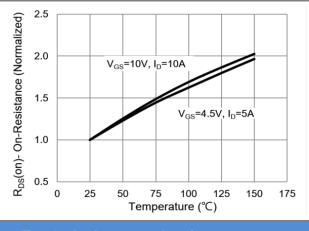
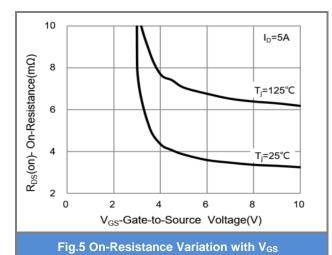


Fig.4 On-Resistance vs. Junction temperature



I_{SD}-Source to Drain Current(A) 0.01 0.6 1.2 V_{SD}-Source-to-Drain Voltage(V)

T_i=25°C

T_i=125°C

Fig.6 Source-Drain Diode Forward Voltage

100

10

1

0.1



TYPICAL CHARACTERISTIC CURVES

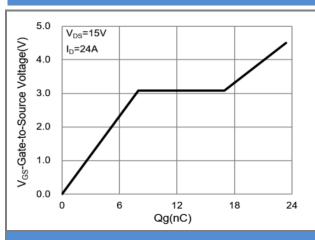


Fig.7 Gate-Charge Characteristics

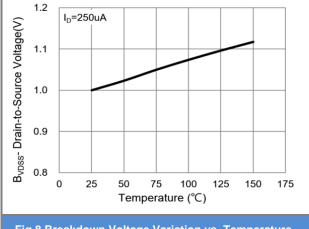


Fig.8 Breakdown Voltage Variation vs. Temperature

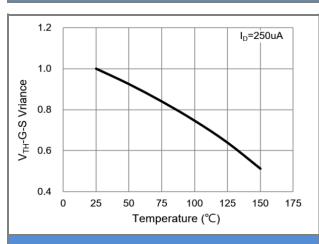


Fig.9 Threshold Voltage Variation with Temperature

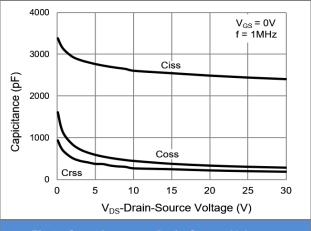


Fig.10 Capacitance vs. Drain-Source Voltage

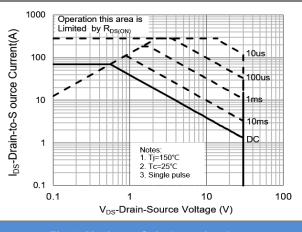


Fig.11 Maximum Safe Operating Area



TYPICAL CHARACTERISTIC CURVES

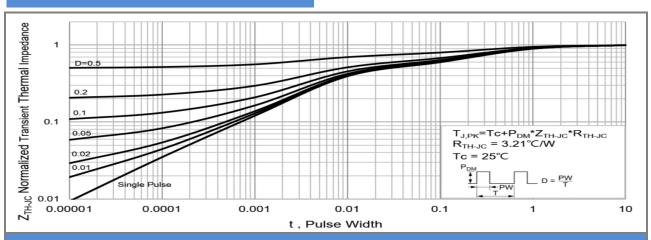


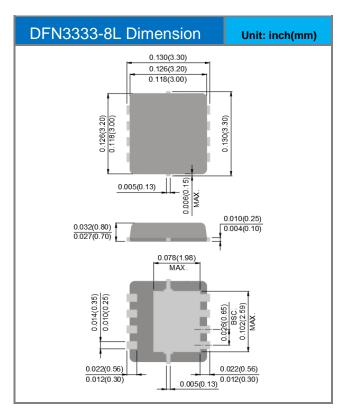
Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

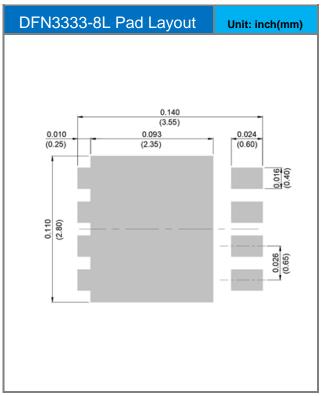


Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4402P-AU_R2_000A1	DFN3333-8L	5K pcs / 13" reel	4402	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout







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